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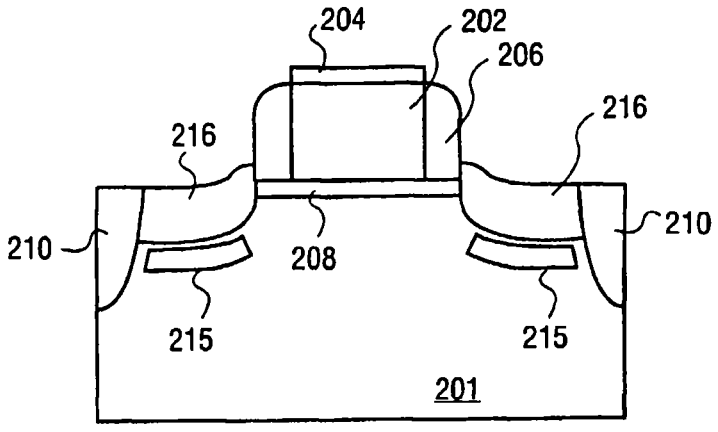
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ACTION

(54) Title: FIELD EFFECT TRANSISTOR STRUCTURE WITH PARTIALLY ISOLATED SOURCE/DRAIN JUNCTIONS AND METHODS OF MAKING SAME



(57) Abstract: A microelectronic structure includes at least one source/drain terminal of a first conductivity type that is partially isolated from a region of semiconductor material of a second conductivity type. In a further aspect of the invention, a process for forming a microelectronic structure, such as a MOSFET, having at least one source/drain terminal of a first conductivity type that is partially isolated from a region of semiconductor material of a second conductivity type includes forming a recess having a surface, forming a dielectric material over a portion of the surface of the recess, and back-filling the recess to form a source/drain terminal.

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